

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	$3\Omega @ V_{GS} = 4.5V$	250mA
30V	$5\Omega @ V_{GS} = 4.0V$	200mA
	7Ω @ V _{GS} = 2.5V	100mA

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Motor Control
- DC-DC Converters
- Backlighting

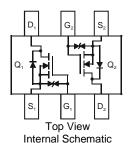
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)









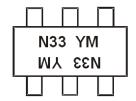
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN33D8LDWQ-7	SOT363	3,000/Tape & Reel
DMN33D8LDWQ-13	SOT363	10.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



N33 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	201	9	2020		2021	20	22	2023		2024	2	2025
Code	G		Н			,	J	K		L		M
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 4.5V	I _D	250 200	mA	
Maximum Continuous Body Diode Forward Current	t (Note 6)	Is	0.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%))	I _{DM}	0.8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	D	0.35	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P _D	0.22	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	360	°C/W	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	126	- C/VV	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ $T_A = \pm 25$ °C, unless otherwise specified.)

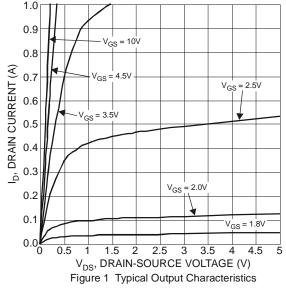
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}		_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.8	_	1.5	V	$V_{DS} = 3V, I_D = 100 \mu A$	
			_	2.4		$V_{GS} = 10V, I_D = 250mA$	
Static Drain-Source On-Resistance	_	_	_	3.0	Ω	$V_{GS} = 4.5V, I_D = 250mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	5.0	12	$V_{GS} = 4.0V, I_D = 10mA$	
		_	_	7.0		$V_{GS} = 2.5V, I_D = 5mA$	
Diode Forward Voltage	V_{SD}	_	_	1.2	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)	•					•	
Input Capacitance	C _{iss}	1	48	_	pF)/ 5)/)/ O)/	
Output Capacitance	Coss	1	11	_	pF	$V_{DS} = 5V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss		8	_	pF	1 - 1.01/11/12	
Gate Resistance	R_g	_	57	_	Ω	f=1MHz, V _{GS} =0V, V _{DS} =0V	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	0.55	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	_	1.23	_	nC	\\	
Gate-Source Charge	Q _{qs}	_	0.14	_	nC	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge	Q _{qd}	_	0.14	_	nC		
Turn-On Delay Time	t _{D(ON)}		2.9	_	ns		
Turn-On Rise Time	t _R		2.6	_	ns	V _{DD} = 30V, V _{GS} = 10V,	
Turn-Off Delay Time			18.2	_	ns	$R_G = 25\Omega, I_D = 200 \text{mA}$	
Turn-Off Fall Time		_	13.6	_	ns		

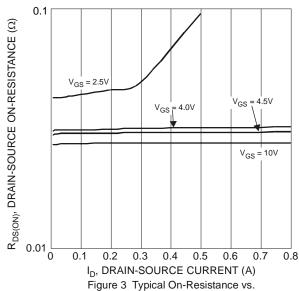
Notes: 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.







Drain Current and Gate Voltage

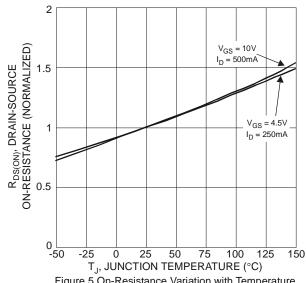
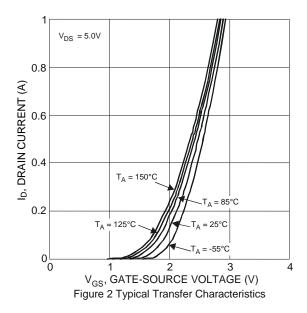
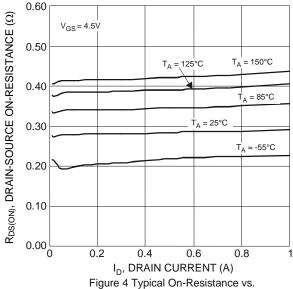


Figure 5 On-Resistance Variation with Temperature



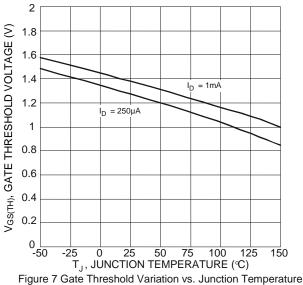


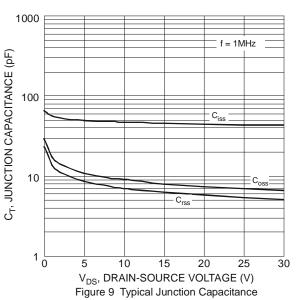
Drain Current and Temperature 0.5 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) $V_{GS} = 4.5V$ $I_{D} = 250 \text{mA}$ 0.4 0.3 $V_{GS} = 10V$ 0.2 I_D = 500mA 0 100 150 -50 25 50 75 125 T_I, JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature

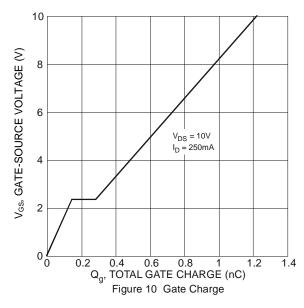








1 0.9 8.0 Is, SOURCE CURRENT (A) 0.7 T_A = 150°C 0.6 T_A = 25°C 0.5 T_A = 125°C 0.4 T_A = -55°C 0.3 $T_A = 85^{\circ}C$ 0.2 0.1 0 0 0.3 0.6 0.9 1.2 1.5 V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current



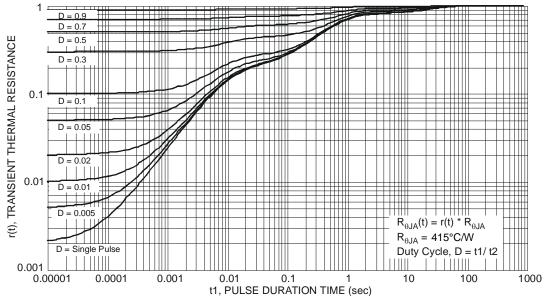


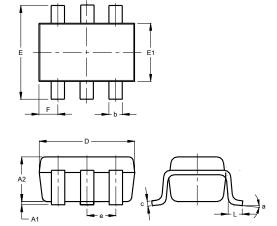
Figure 11 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363

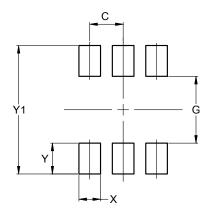


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	C	.650 E	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value (in mm)			
С	0.650			
G	1.300			
Х	0.420			
Υ	0.600			
Y1	2.500			



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